

the main surface of the semiconductor substrate; forming an insulating film on the exposed main surface of the semiconductor substrate by at least one of a vaporizer method using H₂O as an oxidizer, an oxyhydrogen combustion method, and a wet oxidation method performed at temperatures not lower than 950°C; and forming impurity diffused layers on both sides of the respective gate electrodes in the semiconductor substrate.

Page 6, lines 11-19, please replace the paragraph with the following text:

According to another aspect of the present invention, there is provided a semiconductor device manufacturing method comprising forming a gate insulating film in an oxynitride form on a main surface of a semiconductor substrate; forming gate electrodes on the gate insulating film; making a nitrogen concentration of the gate insulating film except under the gate electrodes lower than a nitrogen concentration of the gate insulating film which lies under the gate electrodes by oxidizing the gate electrodes and the gate insulating film by at least one of a vaporizer method using H₂O as an oxidizer, an oxyhydrogen combustion method, and a wet oxidation method performed at temperatures not lower than 950°C; and forming impurity diffused layers on both sides of the respective gate electrodes in the semiconductor substrate.

Page 6, lines 20-28, please replace the paragraph with the following text:

According to still another aspect of the present invention, there is provided a semiconductor device manufacturing method comprising forming a gate insulating film in an oxynitride form on a main surface of a semiconductor substrate; forming gate electrodes on the gate insulating film; forming a post oxidation film on the main surface of the semiconductor substrate except under the gate electrodes by at least one of a vaporizer method using H₂O as an oxidizer, an oxyhydrogen combustion method, and a wet oxidation method performed at temperatures not lower than 950°C; oxynitrifying the post oxidation